

Silicon NPN Epitaxial

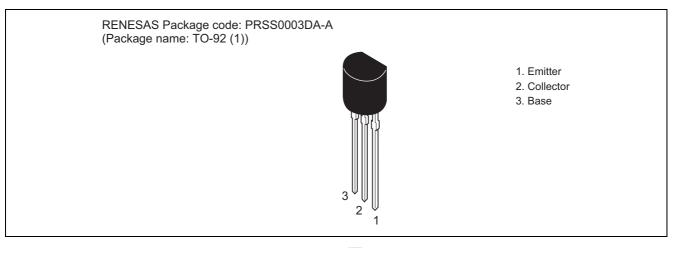
REJ03G0765-0200 (Previous ADE-208-1134) Rev.2.00 Aug.10.2005

Application

• Low frequency power amplifier

• Complementary pair with 2SB561

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	25	V
Collector to emitter voltage	V _{CEO}	20	V
Emitter to base voltage	V _{EBO}	5	V
Collector current	Ι _C	0.7	А
Collector peak current	i _{C(peak)}	1.0	А
Collector power dissipation	Pc	0.5	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C



Electrical Characteristics

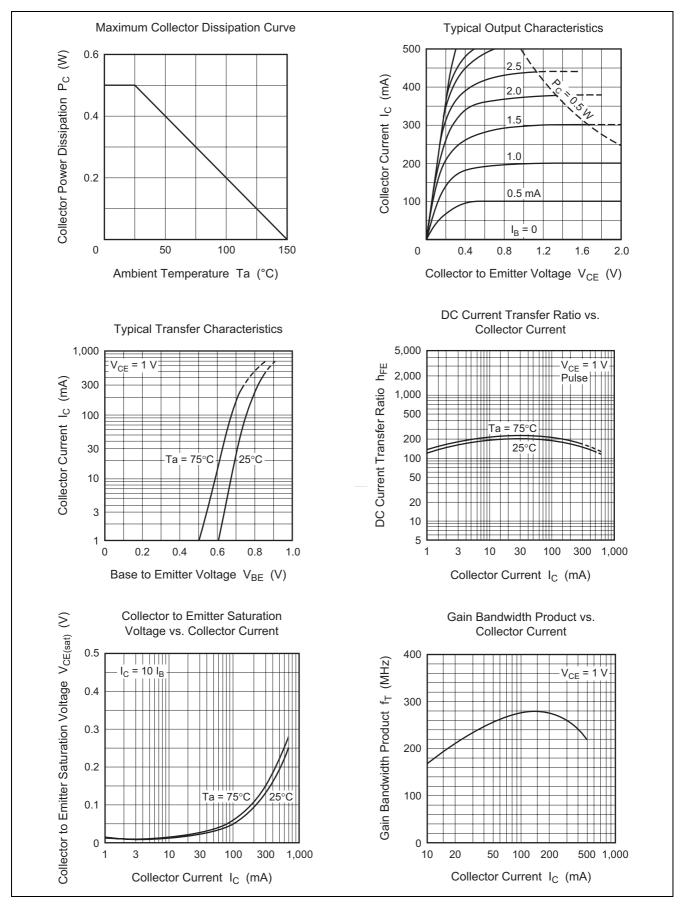
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	25		—	V	$I_{C} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	V _{(BR)CEO}	20		_	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	V _{(BR)EBO}	5		—	V	$I_E = 10 \ \mu A, \ I_C = 0$
Collector cutoff current	I _{CBO}	_		1.0	μA	$V_{CB} = 20 V, I_E = 0$
DC current transfer ratio	h _{FE} * ¹	85	—	240		$V_{CE} = 1 V$, $I_C = 0.15 A$ (Pulse test)
Collector to emitter saturation voltage	V _{CE(sat)}	—	0.19	0.5	V	$I_{C} = 0.5 \text{ A}, I_{B} = 0.05 \text{ A}$ (Pulse test)
Base to emitter voltage	V_{BE}	—	0.76	1.0	V	$V_{CE} = 1 V, I_C = 0.15 A$ (Pulse test)
Gain bandwidth product	f⊤	—	280	_	MHz	$V_{CE} = 1 V$, $I_C = 0.15 A$ (Pulse test)
Collector output capacitance	Cob		12		pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Note: 1. The 2SD467 is grouped by h_{FE} as follows.

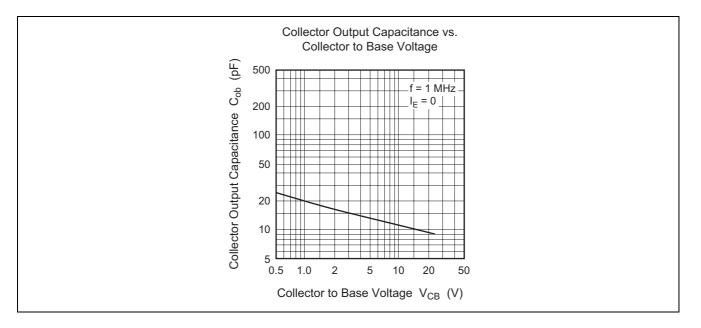
В	С		
85 to170	120 to 240		



Main Characteristics

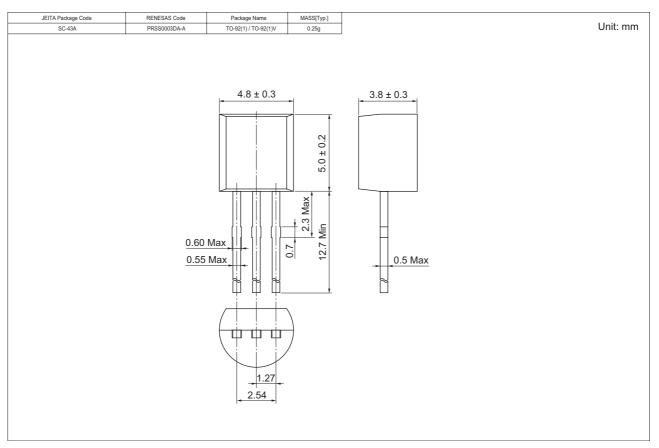








Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SD467BTZ-E	2500	Hold Box, Radial Taping
2SD467CTZ-E		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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